

DESCRIPTION:

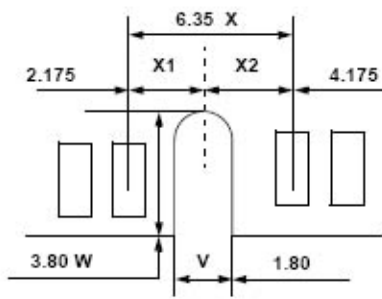
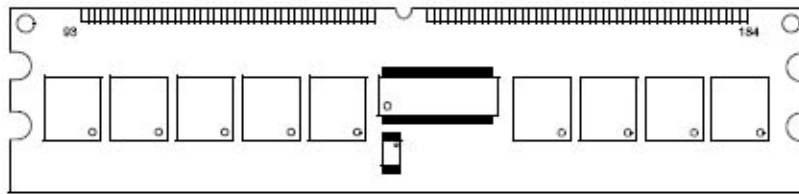
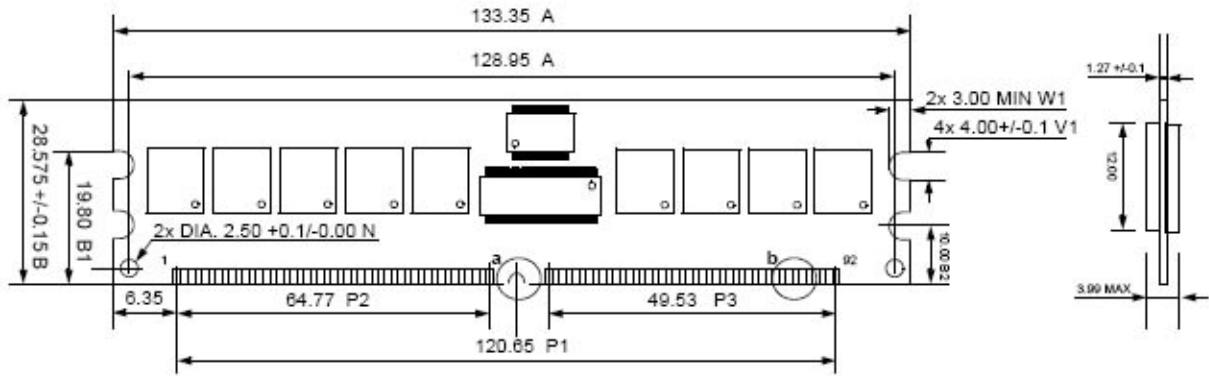
This document describes Aplus 128M x 72-bit 1GB DDR400 CL3 SDRAM (Synchronous DRAM) Registered ECC memory module. The components on this module include eighteen 128M x 4-bit (4Banks) DDR400 SDRAM in FBGA packages. This 184-pin DIMM uses gold contact fingers and requires +2.6V. The electrical and mechanical specifications are as follows:

FEATURES:

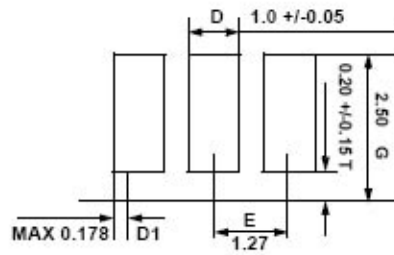
- Power supply: Vdd: $2.6V \pm 0.1V$, Vddq: $2.6V \pm 0.1V$
- All inputs and outputs SSTL_2 compatible
- Max clock Freq: 200Mhz
- Double-data-rate architecture; two data transfers per clock cycle
- Error check correction (ECC) capability
- Bidirectional data strobe (DQS)
- Differential clock inputs (CK and CK)
- DLL aligns DQ and DQS transition with CK transition
- Programmable Read latency 3 (clock)
- Burst Length: 2,4,8 (Interleave/nibble sequential)
- Programmable Burst type (sequential & interleave)
- Timing Reference: CL-tRCD-tRP (3-3-3)
- Edge aligned data output, center aligned data input
- Auto & Self refresh, 7.8us refresh interval (8K/64ms refresh)
- Serial presence detect with EEPROM

PERFORMANCE:

Clock Cycle Time (tCK)	5ns (min.) /10ns (max.)
Row Cycle Time (tRC)	55ns (min.)
Refresh Row Cycle Time (tRFC)	70ns (min.)
Row Active Time (tRAS)	40ns (min.) /70,000ns (max.)
Operating Temperature	0°C to 70 °C
Storage Temperature	-55 °C to +150 °C



Detail A



Detail B